

750V 75A Trench FS Gen.7 IGBT

General Description

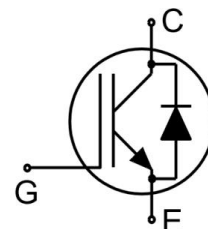
Using NCE's proprietary high density trench gate design and advanced FS (Field Stop) Gen.7 technology, the 750V Trench FS Gen.7 IGBT offers superior conduction and switching performances, and easy parallel operation.

Features

- Trench field stop Gen.7 Technology
- Low saturation voltage: $V_{CEsat} = 1.50V(Typ.) @ I_C = 75 A$
- High speed switching, low switching losses
- Maximum junction temperature $T_{vjmax} = 175^{\circ}C$
- Tighten parameter distribution
- High ruggedness, temperature stable behavior
- Pb-free lead plating; RoHS compliant

Application

- PV power
- Three-level Solar String Inverter
- UPS



Schematic diagram

Package Marking and Ordering Information

Device	Device Package	Device Marking
NCE75ED75BT	TO-247-3L	NCE75ED75BT



TO-247-3L

Absolute Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CES}	Collector-Emitter Voltage	750	V
V_{GES}	Gate- Emitter Voltage	± 30	V
I_C	Collector Current	150	A
	Collector Current @ $T_C = 100^{\circ}C$	75	A
I_{Cpuls}	Pulsed Collector Current, t_p limited by T_{jmax}	262	A
-	Turn off safe operating area, $V_{CE}=750V, T_j=175^{\circ}C$	262	A
I_F	Diode Continuous Forward Current @ $T_C = 100^{\circ}C$	75	A
I_{FM}	Diode Maximum Forward Current	262	A
P_D	Power Dissipation @ $T_C = 25^{\circ}C$	402	W
	Power Dissipation @ $T_C = 100^{\circ}C$	201	W
T_{stg}	Storage Temperature	-55 to +150	$^{\circ}C$
T_{vj}	Operating junction temperature	-40 to +175	$^{\circ}C$
T_L	Maximum Temperature for Soldering	260	$^{\circ}C$

Thermal Characteristic

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction to case for IGBT	0.38	$^{\circ}\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to case for Diode	0.43	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	40	$^{\circ}\text{C/W}$

Electrical Characteristics ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions		Value			Units
				Min.	Typ.	Max.	
Static Characteristics							
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	V _{GE} =0V, I _{CE} =1mA		750	--	--	V
I _{CES}	Collector-Emitter Leakage Current	V _{GE} =0V, V _{CE} =750V		--	--	15	uA
I _{GES(F)}	Gate to Emitter Forward Leakage	V _{GE} =+30V, V _{CE} =0V		--	--	100	nA
I _{GES(R)}	Gate to Emitter Reverse Leakage	V _{GE} =-30V, V _{CE} =0V		--	--	100	nA
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C =40A	T _J =25°C	--	1.20	--	V
		V _{GE} =15V	T _J =150°C	--	1.30	--	V
		I _C =75A	T _J =25°C	--	1.50	2.0	V
		V _{GE} =15V	T _J =150°C	--	1.80	--	V
V _{GE(th)}	Gate Threshold Voltage	I _C =1mA, V _{CE} =V _{GE}		4.0	4.75	5.50	V
Dynamic Characteristics							
C _{ies}	Input Capacitance	V _{CE} =25V, V _{GE} =0V, f=1MHz		3750	4700	5650	pF
C _{oes}	Output Capacitance			--	153	--	
C _{res}	Reverse Transfer Capacitance			--	27	--	
Q _g	Total Gate Charge	V _{CE} =480V, I _C =75A, V _{GE} =15V		--	129	--	nC
Q _{ge}	Gate to Emitter Charge			--	34	--	
Q _{gc}	Gate to Collector Charge			--	46	--	
R _g	Internal Gate Resistance	f=1MHz		--	0.5	--	Ω
Switching Characteristics							
t _{d(on)}	Turn-on Delay Time	V _{CE} =400V, I _C =75A, V _{GE} =0/15V, R _g =9.8Ω, Inductive Load, T _J =25°C		--	31	--	ns
t _r	Rise Time			--	39	--	
t _{d(off)}	Turn-Off Delay Time			--	240	--	
t _f	Fall Time			--	80	--	
E _{on}	Turn-On Switching Loss			--	2.47	--	mJ
E _{off}	Turn-Off Switching Loss			--	1.78	--	
E _{ts}	Total Switching Loss			--	4.36	--	

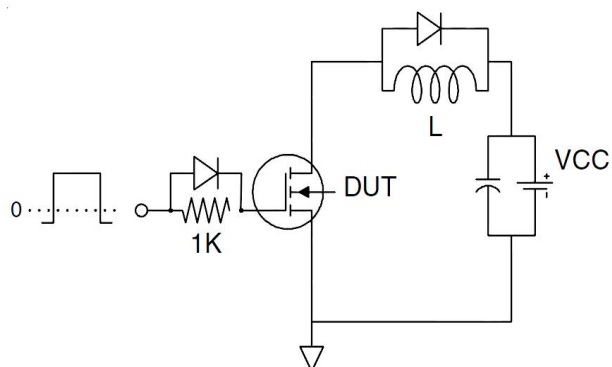
Electrical Characteristics of the Diode ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions		Rating			Units
				Min.	Typ.	Max.	
V_{FM}	Diode Forward Voltage	$I_F = 75\text{A}$	$T_j = 25^\circ\text{C}$	--	1.80	2.50	V
			$T_j = 150^\circ\text{C}$	--	1.50	--	
T_{rr}	Reverse Recovery Time	$I_F = 75\text{A}, R_g = 9.8\Omega,$ $T_j = 25^\circ\text{C}$		--	134	--	ns
I_{RRM}	Diode Peak Reverse Recovery Current			--	16.5	--	A
Q_{rr}	Reverse Recovery Charge			--	1.03	--	μC
E_{rec}	Reverse recovery energy			--	0.41	--	mJ

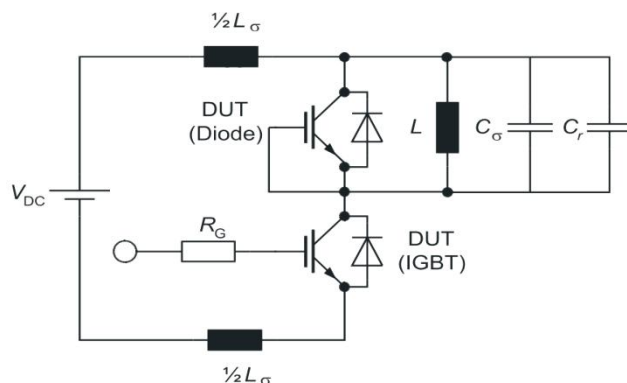
Note: For optimum lifetime and reliability, NCE recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Test Circuit

1) Gate Charge Test Circuit

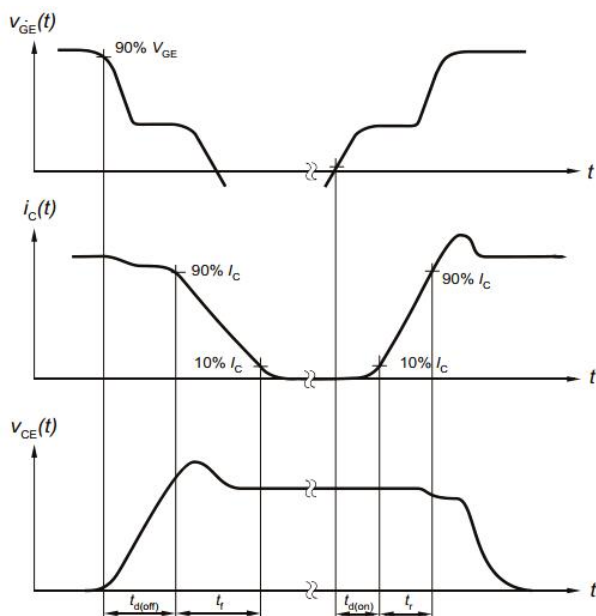


2) Switch Time Test Circuit

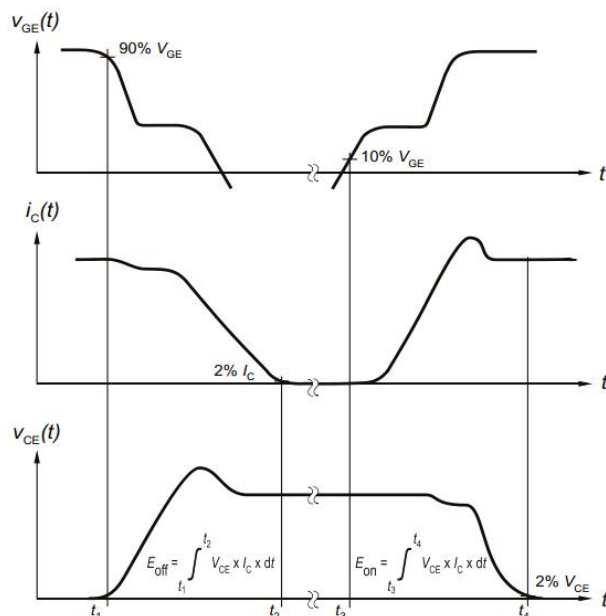


Switching characteristics

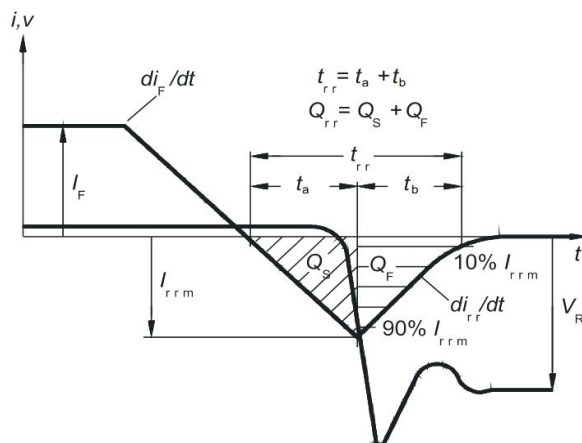
1) Definition of switching times



2) Definition of switching losses



3) Definition of diode switching characteristics



Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

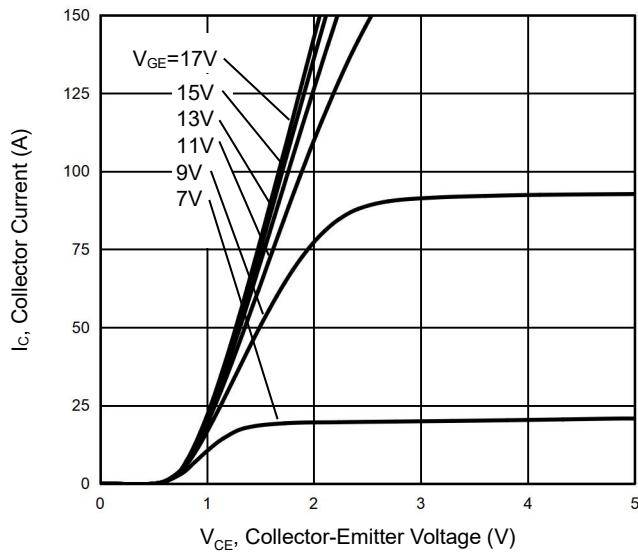


Figure 2 Transfer Characteristics

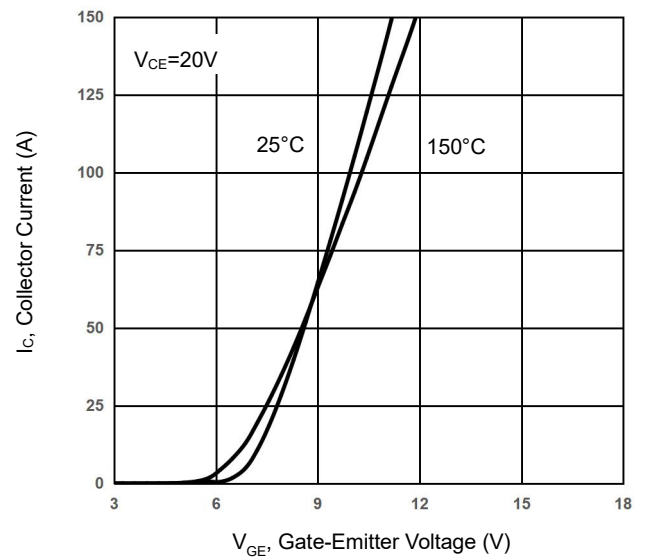


Figure 3 $V_{CE(sat)}$ vs. Temperature

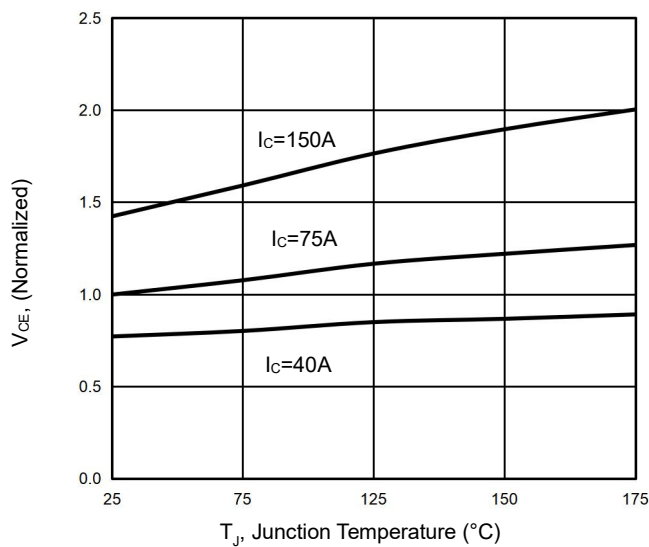


Figure 4 Saturation Voltage vs. V_{GE}

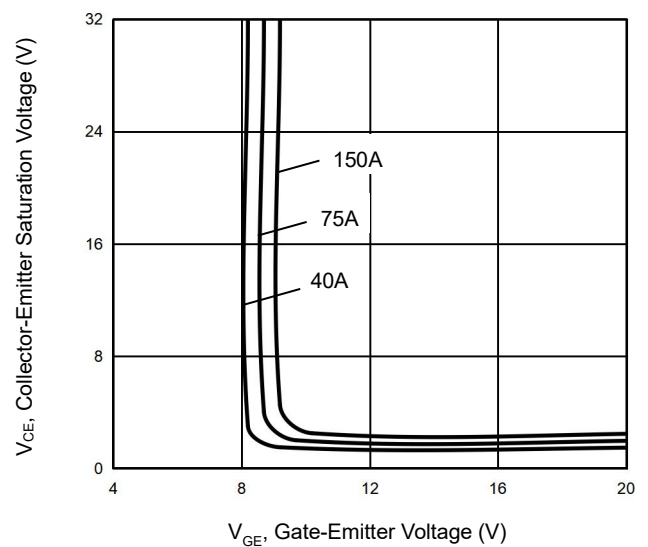


Figure 5 Capacitance Characteristics

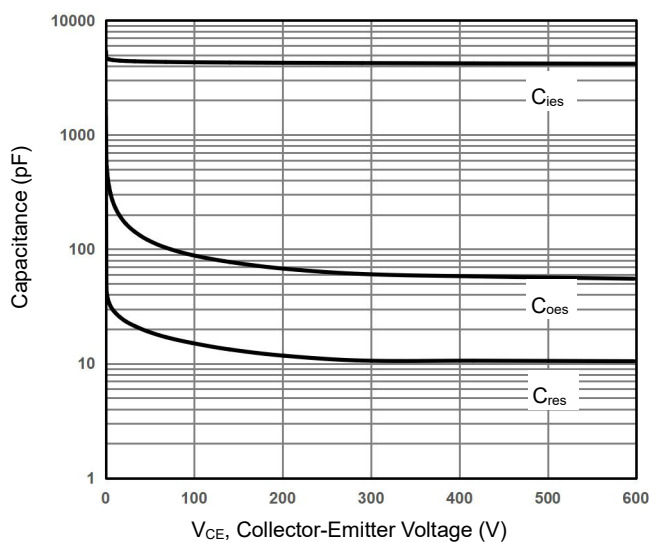
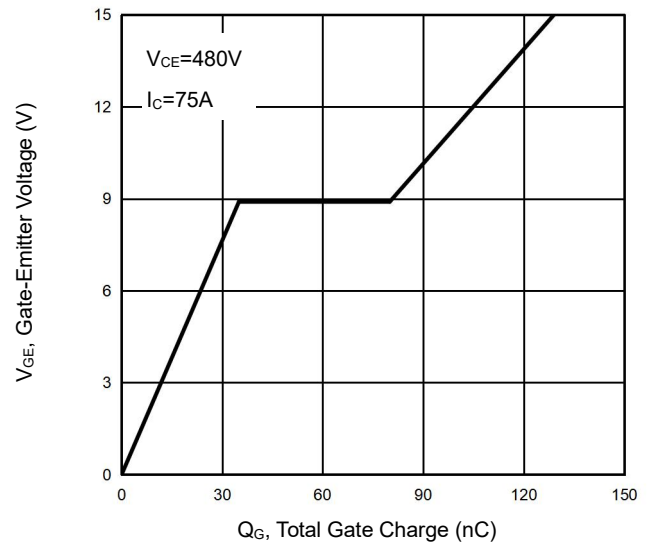


Figure 6 Gate Charge Wave Form



Typical Electrical and Thermal Characteristics

Figure 7 Forward Characteristics

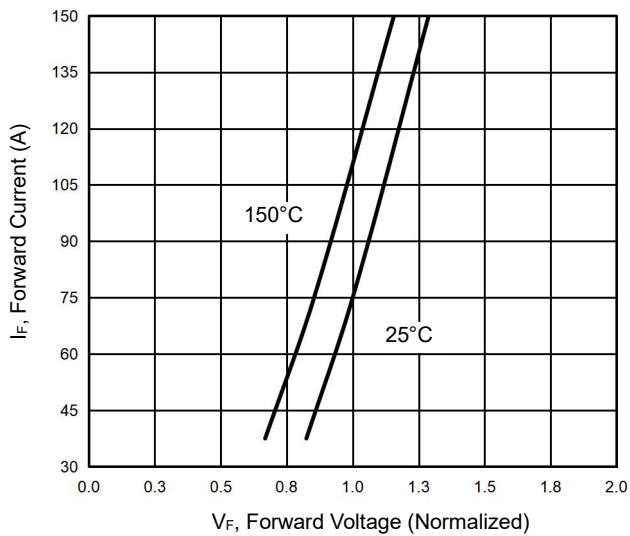


Figure 8 V_F vs. Temperature

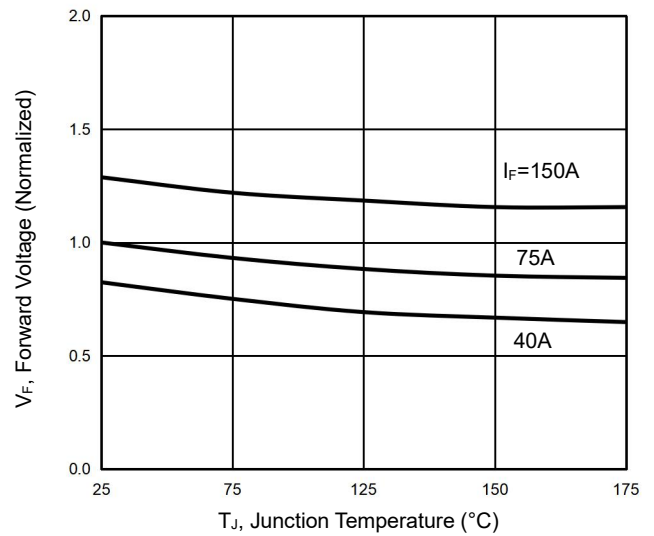


Figure 9 Gate-Emitter Threshold Voltage as a Function of Junction Temperature

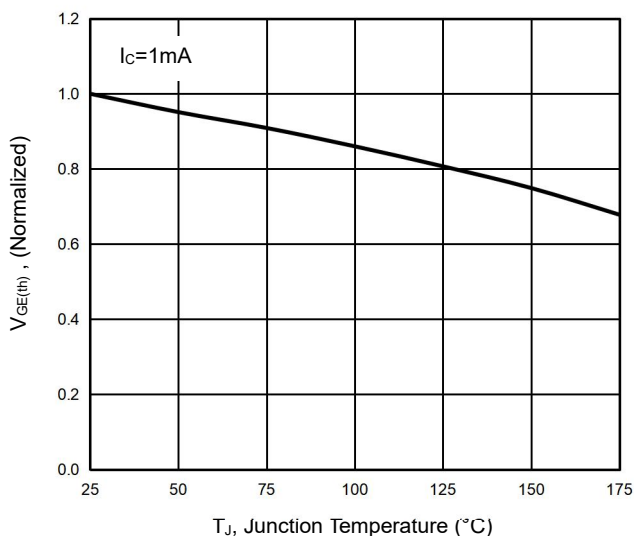


Figure 10 $V_{(BR)CES}$ vs. Temperature

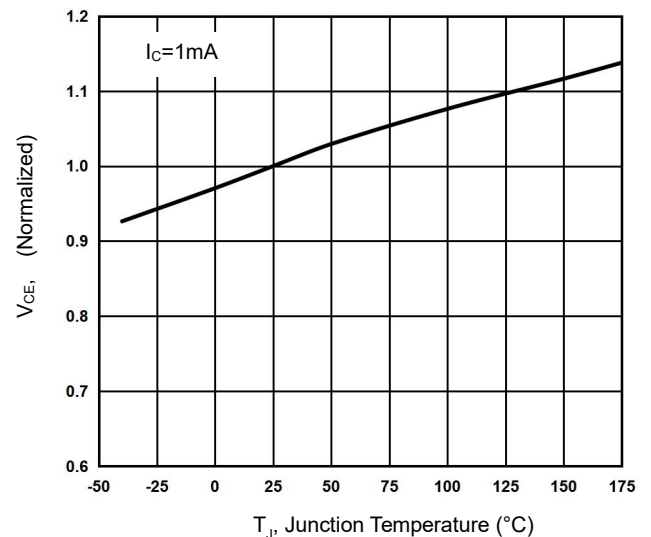


Figure 11 Switching Loss vs. R_G

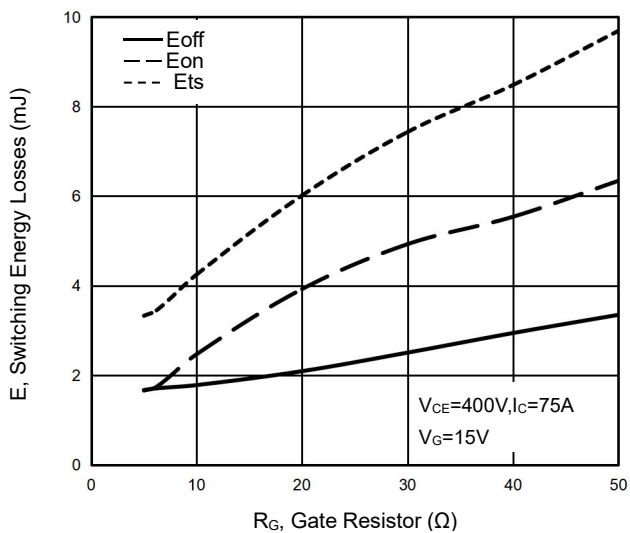
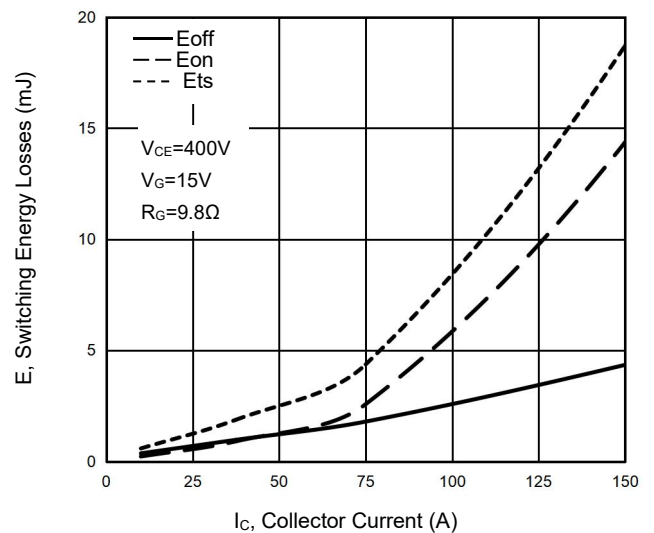
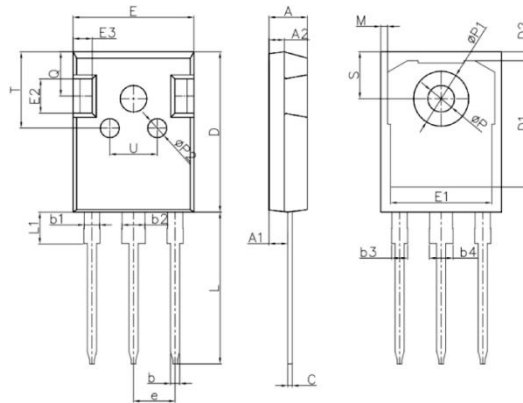


Figure 12 Switching Loss vs. Collector Current

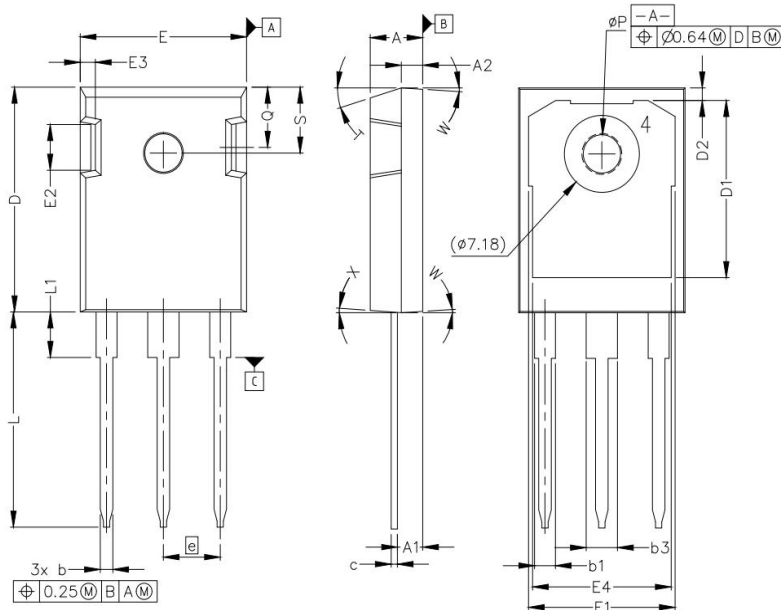


TO-247-3L(E) Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.90	5.10	0.19	0.20
A1	2.31	2.51	0.09	0.10
A2	1.90	2.10	0.07	0.08
b	1.16	1.26	0.05	0.06
b1	1.96	2.06	0.08	0.09
b2	2.96	3.06	0.12	0.13
b3	--	2.25	--	0.09
b4	--	3.25	--	0.13
c	0.59	0.66	0.02	0.03
D	20.90	21.10	0.82	0.83
D1	16.25	16.85	0.64	0.66
D2	1.05	1.35	0.04	0.05
E	15.70	15.90	0.62	0.63
E1	13.10	13.50	0.52	0.53
E2	4.40	4.60	0.17	0.18
E3	2.40	2.60	0.09	0.10
e	5.436 BSC		0.214 BSC	
L	19.80	20.10	0.78	0.79
L1	--	4.30	--	0.17
M	0.35	0.95	0.01	0.04
P	3.40	3.60	0.13	0.14
P1	7.00	7.40	0.28	0.29
P2	2.40	2.60	0.09	0.10
Q	5.60	6.00	0.22	0.24
S	6.05	6.25	0.24	0.25
T	9.80	10.20	0.39	0.40
U	6.00	6.40	0.24	0.25

TO-247-3L(B) Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	0.19	0.21
A1	2.29	2.54	0.09	0.10
A2	1.91	2.16	0.08	0.09
b	1.07	1.33	0.04	0.05
b1	1.91	2.41	0.08	0.10
b3	2.87	3.38	0.11	0.13
c	0.55	0.68	0.02	0.03
D	20.80	21.10	0.82	0.83
D1	16.25	17.65	0.64	0.70
D2	0.95	1.25	0.04	0.05
E	15.75	16.13	0.62	0.64
E1	13.10	14.15	0.52	0.56
E2	3.68	5.10	0.15	0.20
E3	1.00	1.90	0.04	0.08
E4	12.38	13.43	0.49	0.53
e	5.44 BSC		0.21 BSC	
L	19.81	20.32	0.78	0.80
L1	4.10	4.40	0.16	0.17
ØP	3.51	3.65	0.14	0.15
Q	5.49	6.00	0.22	0.24
S	6.04	6.30	0.24	0.25
T	17.5° REF			
W	3.5° REF			
X	4° REF			

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